

PMV65UNEAR Datasheet



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DiGi Electronics Part Number PMV65UNEAR-DG

Manufacturer Nexperia USA Inc.

Manufacturer Product Number PMV65UNEAR

Description MOSFET N-CH 20V 2.8A TO236AB

Detailed Description N-Channel 20 V 2.8A (Ta) 940mW (Ta) Surface Mou

nt TO-236AB



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Purchase and inquiry

Manufacturer Product Number:	Manufacturer:
PMV65UNEAR	Nexperia USA Inc.
Series:	Product Status:
	Active
FET Type:	Technology:
N-Channel	MOSFET (Metal Oxide)
Drain to Source Voltage (Vdss):	Current - Continuous Drain (Id) @ 25°C:
20 V	2.8A (Ta)
Drive Voltage (Max Rds On, Min Rds On):	Rds On (Max) @ Id, Vgs:
1.8V, 4.5V	73mOhm @ 2.8A, 4.5V
Vgs(th) (Max) @ ld:	Gate Charge (Qg) (Max) @ Vgs:
1V @ 250μA	6 nC @ 4.5 V
Vgs (Max):	Input Capacitance (Ciss) (Max) @ Vds:
±8V	291 pF @ 10 V
FET Feature:	Power Dissipation (Max):
	940mW (Ta)
Operating Temperature:	Grade:
-55°C ~ 150°C (TJ)	Automotive
Qualification:	Mounting Type:
AEC-Q100	Surface Mount
Supplier Device Package:	Package / Case:
TO-236AB	TO-236-3, SC-59, SOT-23-3
Base Product Number:	
PMV65	

Environmental & Export classification

8541.21.0095

RoHS Status:	Moisture Sensitivity Level (MSL):
ROHS3 Compliant	1 (Unlimited)
REACH Status:	ECCN:
REACH Unaffected	EAR99
HTSUS:	



PMV65UNEA

20 V, N-channel Trench MOSFET 17 March 2017

Product data sheet

1. General description

N-channel enhancement mode Field-Effect Transistor (FET) in a small SOT23 (TO-236AB) Surface-Mounted Device (SMD) plastic package using Trench MOSFET technology.

2. Features and benefits

- Trench MOSFET technology
- · Low threshold voltage
- · Enhanced power dissipation capability of 940 mW
- ElectroStatic Discharge (ESD) protection > 2KV HBM
- AEC-Q101 qualified

3. Applications

- LED driver
- Power management
- Low-side loadswitch
- Switching circuits

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V_{DS}	drain-source voltage	T _j = 25 °C		-	-	20	V
V_{GS}	gate-source voltage	T _j = 25 °C; T _{amb} = 25 °C		-8	-	8	V
I _D	drain current	V _{GS} = 4.5 V; T _{amb} = 25 °C	[1]	-	-	2.8	Α
Static characte	Static characteristics						
R _{DSon}	drain-source on-state resistance	V_{GS} = 4.5 V; I_D = 2.8 A; T_j = 25 °C		-	63	73	mΩ

[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated, mounting pad for drain 6 cm².



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5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate	3	D -
2	S	source		
3	D	drain	1 2 TO-236AB (SOT23)	G S 017aaa255

6. Ordering information

Table 3. Ordering information

Type number	Package					
	Name	Description	Version			
PMV65UNEA	TO-236AB	plastic surface-mounted package; 3 leads	SOT23			

7. Marking

Table 4. Marking codes

Type number	Marking code[1]
PMV65UNEA	EM%

[1] % = placeholder for manufacturing site code

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V _{DS}	drain-source voltage	T _j = 25 °C		-	20	V
V _{GS}	gate-source voltage	T _j = 25 °C; T _{amb} = 25 °C		-8	8	V
I _D	drain current	V _{GS} = 4.5 V; T _{amb} = 25 °C	[1]	-	2.8	Α
		V _{GS} = 4.5 V; T _{amb} = 100 °C	[1]	-	1.8	Α
I _{DM}	peak drain current	T_{amb} = 25 °C; single pulse; $t_p \le 10 \mu s$		-	11	Α
E _{DS(AL)S}	non-repetitive drain- source avalanche energy	$T_{j(init)}$ = 25 °C; I_D = 0.3 A; DUT in avalanche (unclamped)		-	5.6	mJ
P _{tot}	total power dissipation	T _{amb} = 25 °C	[2]	-	490	mW
			[1]	-	940	mW
		T _{sp} = 25 °C		-	6.25	W
Tj	junction temperature			-55	150	°C
T _{amb}	ambient temperature			-55	150	°C
T _{stg}	storage temperature			-65	150	°C
Source-drain	n diode					
I _S	source current	T _{amb} = 25 °C	[1]	-	0.9	Α
ESD Maximu	ım rating					
V _{ESD}	electrostatic discharge voltage	НВМ		-	2000	V

^[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated, mounting pad for drain 6 cm².

^[2] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.

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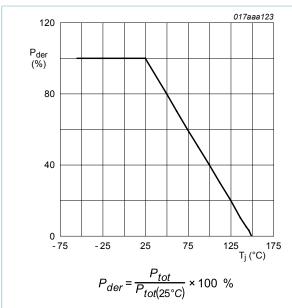


Fig. 1. Normalized total power dissipation as a function of junction temperature

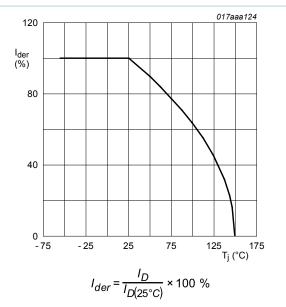


Fig. 2. Normalized continuous drain current as a function of junction temperature

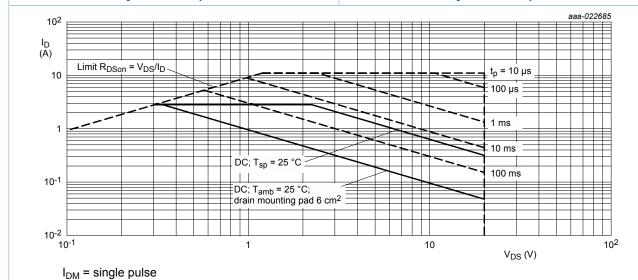


Fig. 3. Safe operating area; junction to ambient; continuous and peak drain currents as a function of drain-source voltage

9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
R _{th(j-a)}	thermal resistance from junction to ambient		[1]	-	221	254	K/W
			[2]	_	116	133	K/W
R _{th(j-sp)}	thermal resistance from junction to solder point			-	17	20	K/W

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- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 6 cm².

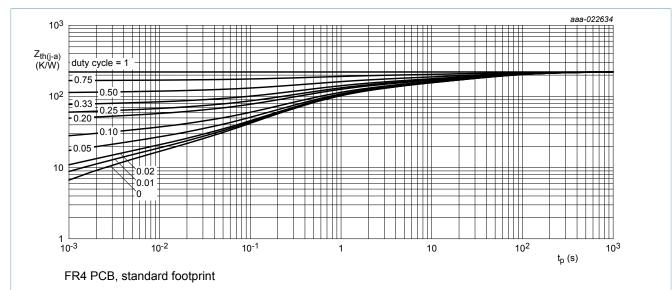


Fig. 4. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

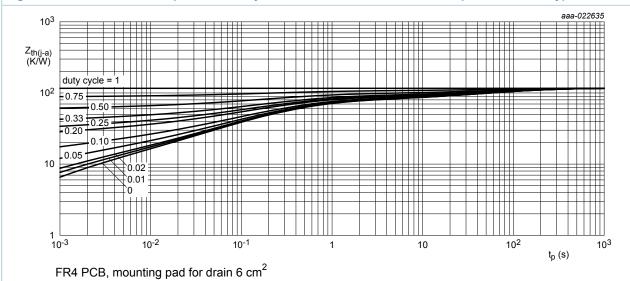


Fig. 5. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

10. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	acteristics					
V _{(BR)DSS}	drain-source breakdown voltage	$I_D = 250 \ \mu\text{A}; \ V_{GS} = 0 \ V; \ T_j = 25 \ ^{\circ}\text{C}$	20	-	-	V
V_{GSth}	gate-source threshold voltage	$I_D = 250 \mu A; V_{DS} = V_{GS}; T_j = 25 ^{\circ}C$	0.45	0.7	1	V
I _{DSS}	drain leakage current	V _{DS} = 20 V; V _{GS} = 0 V	-	-	1	μA
I _{GSS}	gate leakage current	V _{GS} = 8 V; V _{DS} = 0 V; T _j = 25 °C	-	-	10	μΑ
		V_{GS} = -8 V; V_{DS} = 0 V; T_j = 25 °C	-	-	-10	μA
		V _{GS} = 4.5 V; V _{DS} = 0 V; T _j = 25 °C	-	-	5	μΑ
		$V_{GS} = -4.5 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	-	-5	μΑ
DOON	drain-source on-state	$V_{GS} = 4.5 \text{ V}; I_D = 2.8 \text{ A}; T_j = 25 ^{\circ}\text{C}$	-	63	73	mΩ
	resistance	V_{GS} = 4.5 V; I_{D} = 2.8 A; T_{j} = 150 °C	-	93	108	mΩ
		$V_{GS} = 2.5 \text{ V}; I_D = 2.4 \text{ A}; T_j = 25 ^{\circ}\text{C}$	-	71	83	mΩ
		V_{GS} = 1.8 V; I_D = 0.8 A; T_j = 25 °C	-	83	94	mΩ
9 _{fs}	forward transconductance	$V_{DS} = 10 \text{ V}; I_D = 3 \text{ A}; T_j = 25 ^{\circ}\text{C}$	-	11	-	S
R _G	gate resistance	T _j = 25 °C; f = 1 MHz	-	1.8	-	Ω
Dynamic ch	naracteristics					
Q _{G(tot)}	total gate charge	$V_{DS} = 10 \text{ V}; I_D = 2.8 \text{ A}; V_{GS} = 4.5 \text{ V};$	-	3.8	6	nC
Q_{GS}	gate-source charge	T _j = 25 °C	-	0.3	-	nC
Q_{GD}	gate-drain charge		-	0.9	-	nC
C _{iss}	input capacitance	$V_{DS} = 10 \text{ V}; f = 1 \text{ MHz}; V_{GS} = 0 \text{ V};$	-	291	-	pF
C _{oss}	output capacitance	T _j = 25 °C	-	52	-	pF
C _{rss}	reverse transfer capacitance		-	43	-	pF
t _{d(on)}	turn-on delay time	V_{DS} = 10 V; I_{D} = 2.8 A; V_{GS} = 4.5 V;	-	8	-	ns
t _r	rise time	$R_{G(ext)} = 6 \Omega; T_j = 25 ^{\circ}C$	-	23	-	ns
t _{d(off)}	turn-off delay time		-	35	-	ns
t _f	fall time		-	12	-	ns
Source-dra	in diode					
V _{SD}	source-drain voltage	I _S = 0.9 A; V _{GS} = 0 V; T _i = 25 °C	_	0.7	1.2	V

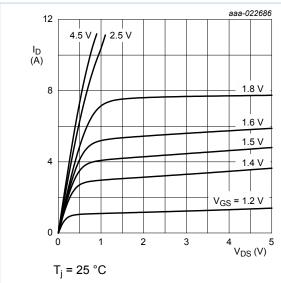


Fig. 6. Output characteristics: drain current as a function of drain-source voltage; typical values

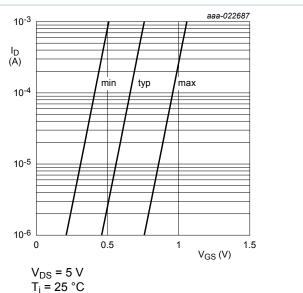


Fig. 7. Sub-threshold drain current as a function of gate-source voltage

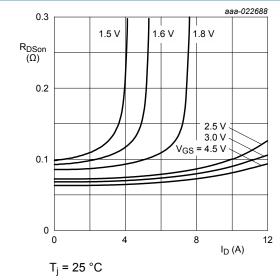


Fig. 8. Drain-source on-state resistance as a function of drain current; typical values

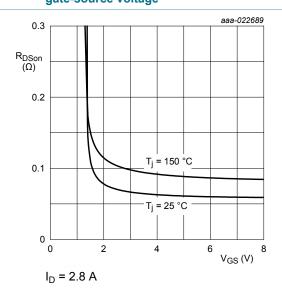


Fig. 9. Drain-source on-state resistance as a function of gate-source voltage; typical values

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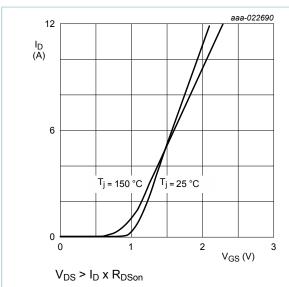


Fig. 10. Transfer characteristics: drain current as a function of gate-source voltage; typical values

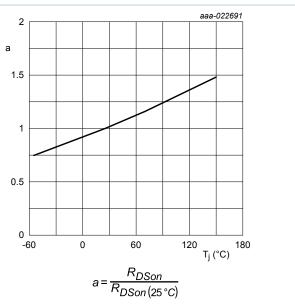


Fig. 11. Normalized drain-source on-state resistance as a function of ambient temperature; typical values

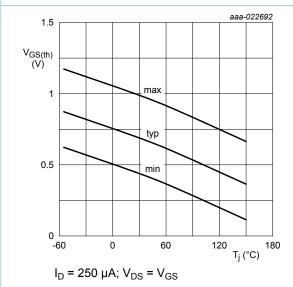


Fig. 12. Gate-source threshold voltage as a function of ambient temperature

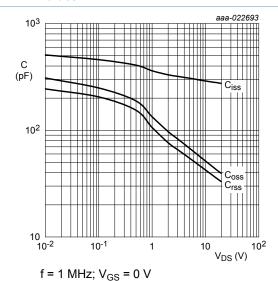


Fig. 13. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

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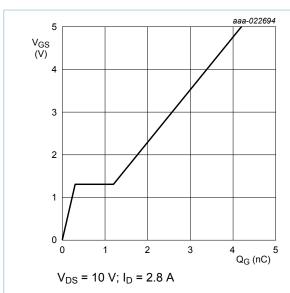


Fig. 14. Gate-source voltage as a function of gate charge; typical values

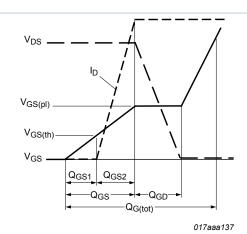


Fig. 15. Gate charge waveform definitions

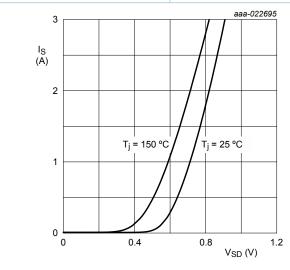


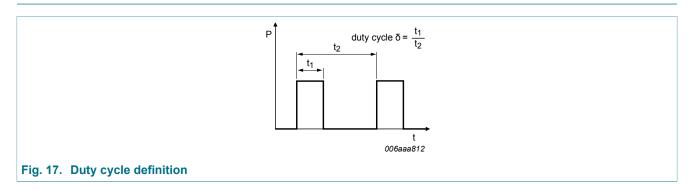
Fig. 16. Source current as a function of source-drain voltage; typical values

 $V_{GS} = 0 V$

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11. Test information

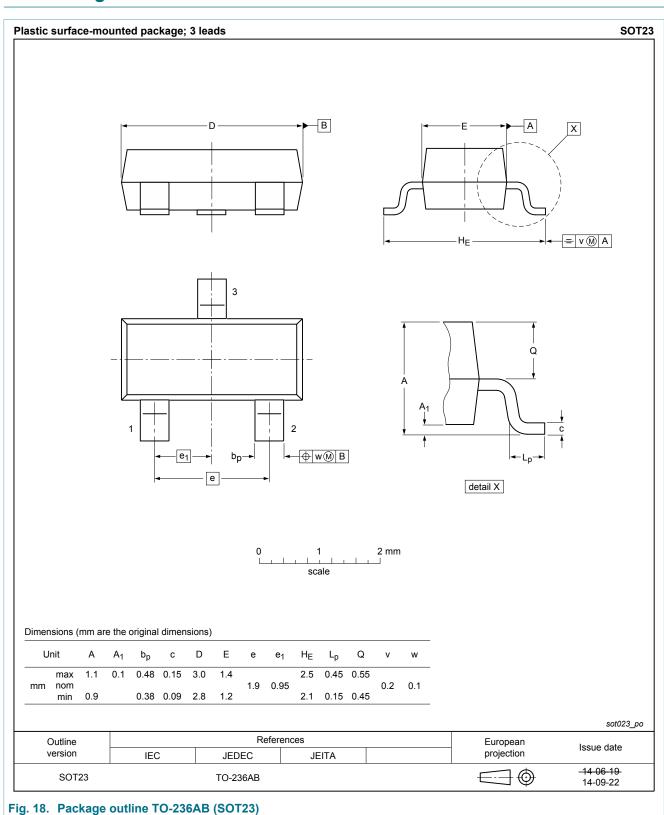


Quality information

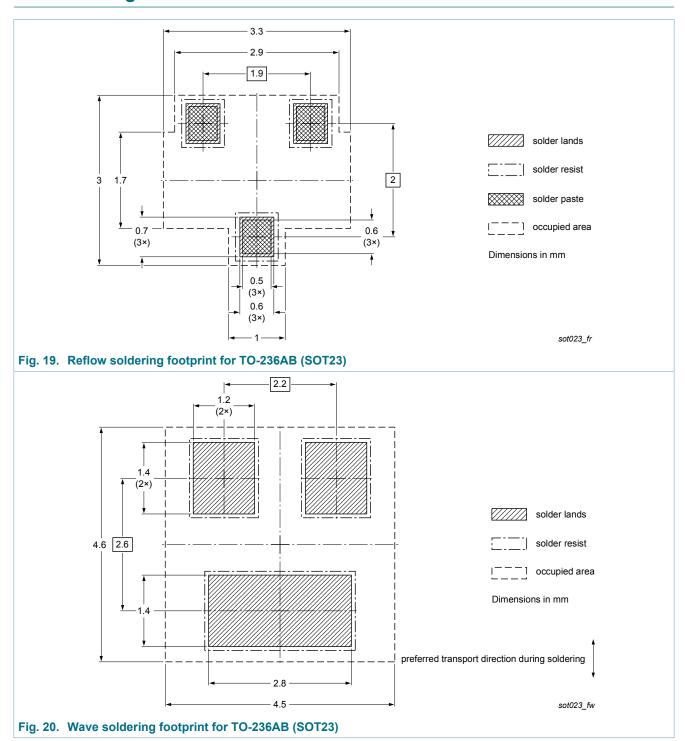
This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard Q101 - Stress test qualification for discrete semiconductors, and is suitable for use in automotive applications.

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12. Package outline



13. Soldering



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PMV65UNEA

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14. Revision history

Table 8. Revision history

Data sheet ID	Release date	Data sheet status	Change notice	Supersedes
PMV65UNEA v.1	20170317	Product data sheet	-	-

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15. Legal information

Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- Please consult the most recently issued document before initiating or completing a design.
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